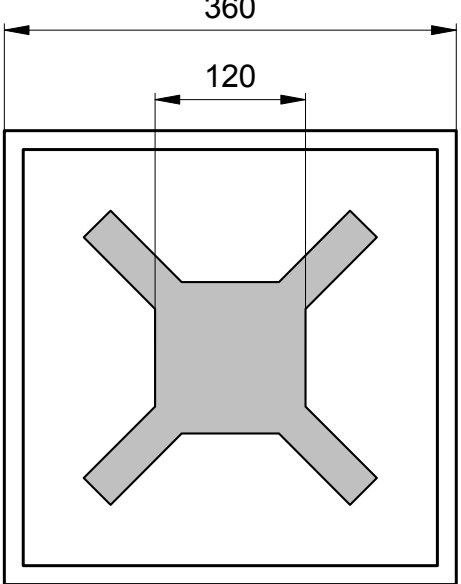


| Radiation | Type | Technology | Electrodes |
|-----------|------|---------------|----------------|
| Infrared | DDH | AlGaAs/AlGaAs | N (cathode) up |

| | | |
|---|--|--|
|  <p style="text-align: center;">LED-05</p> | typ. dimensions (μm) | |
| | <u>typ. thickness</u> 150 (±25) μm | |
| | <u>cathode</u> gold alloy, 1.5 μm | |
| | <u>anode</u> gold alloy, 0.5 μm, dotted, 25% covered | |

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

| Parameter | Test conditions | Symbol | Min | Typ | Max | Unit |
|----------------------------|-------------------------|---------------------------------|-----|-----|-----|------|
| Forward voltage | I _F = 20 mA | V _F | | 1.7 | 2.1 | V |
| Reverse voltage | I _R = 100 μA | V _R | 5 | | | V |
| Radiant power ¹ | I _F = 20 mA | Φ _e | 2.0 | 2.7 | | mW |
| Radiant power ² | I _F = 20 mA | Φ _e | | 5.0 | | mW |
| Peak wavelength | I _F = 20 mA | λ _p | 760 | 770 | 780 | nm |
| Spectral bandwidth at 50% | I _F = 20 mA | Δλ _{0.5} | | 30 | | nm |
| Switching time | I _F = 20 mA | t _r , t _f | | 40 | | ns |

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

| Type | Lot N° | Φ _e (typ) [mW] | V _F (typ) [V] | Quantity |
|------------|--------|---------------------------|--------------------------|----------|
| ELC-770-27 | | | | |

Packing: Chips on adhesive film with wire-bond side on top